8-Bit Dual-Supply Non-Inverting Level Translator

The NLSV8T244 is a 8-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 4.0 mm x 2.0 mm UDFN20
- This is a Pb-Free Device

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins: HBM (Human Body Model) > 6000 V



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



UQFN20 MU SUFFIX CASE 517AK



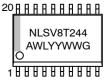
LC = Specific Device Code

M = Date Code

= Pb-Free Package



SOIC-20 DW SUFFIX CASE 751D



A = Assembly Location

WL = Wafer Lot
 YY = Year
 WW = Work Week
 G = Pb-Free Package



TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

L = Wafer Lot

Y = Year

W = Work Week

(Note: Microdot may be in either location)

= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

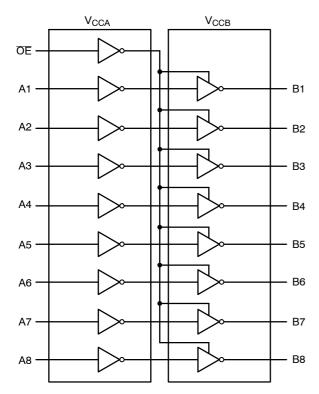


Figure 1. Logic Diagram

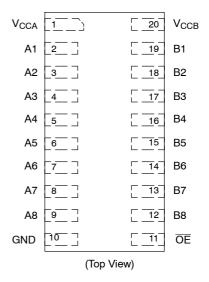


Figure 2. Pin Assignment

TRUTH TABLE

In	Inputs			
ŌĒ	A _n	B _n		
L	L	L		
L	Н	Н		
Н	Х	3-State		

PIN ASSIGNMENT

PIN	FUNCTION
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
V _I	DC Input Voltage	A _n	−0.5 to +5.5		V
V _C	Control Input	ŌĒ	−0.5 to +5.5		V
V _O	DC Output Voltage (Power Down)	B _n	-0.5 to +5.5	V _{CCA} = V _{CCB} = 0	V
	(Active Mode)	B _n	-0.5 to +5.5		٧
	(Tri-State Mode)	B _n	−0.5 to +5.5		V
I _{IK}	DC Input Diode Current		-20	V _I < GND	mA
I _{OK}	DC Output Diode Current		-50	V _O < GND	mA
Io	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100		mA
T _{STG}	Storage Temperature		-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
V _I	Bus Input Voltage		GND	4.5	V
V _C	Control Input	ŌĒ	GND	4.5	V
V _{IO}	Bus Output Voltage (Power Down Mode)	B _n	GND	4.5	V
	(Active Mode)	B _n	GND	V _{CCB}	V
	(Tri-State Mode)	B _n	GND	4.5	V
T _A	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V_{l} , from 30% to 70% of V_{CC} ; V_{CC} = 3.3 V ±0.3 V		0	10	nS

DC ELECTRICAL CHARACTERISTICS

					-40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, \overline{OE})		2.7 – 3.6		2.0	-	
			2.3 – 2.7	1	1.6	-	
			1.4 – 2.3	1	0.65 * V _{CCA}	-	
			0.9 – 1.4		0.9 * V _{CCA}	-	
V _{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	8.0	V
	(An, ŌĒ)		2.7 – 3.6		-	0.8	
			2.3 – 2.7		-	0.7	
			1.4 – 2.3		-	0.35 * V _{CCA}	
			0.9 – 1.4		-	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	-	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	-	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V_{OL}	Output LOW Voltage	I_{OL} = 100 μ A; V_I = V_{IL}	0.9 - 4.5	0.9 – 4.5	-	0.2	٧
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IL}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IL}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		I_{OL} = 12 mA; V_I = V_{IL}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I_{OL} = 18 mA; V_I = V_{IL}	2.3	2.3	-	0.6	
			3.0	3.0	-	0.45	
		I_{OL} = 24 mA; V_I = V_{IL}	3.0	3.0	-	0.6	
lį	Input Leakage Current	V _I = V _{CCA} or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ
l _{OFF}	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
CCA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μΑ
ΔI_{CCA}	Increase in I_{CC} per Input Voltage, Other Inputs at V_{CCA} or GND	$V_I = V_{CCA} - 0.6 V;$ $V_I = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
Δl _{CCB}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 V;$ $V_I = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
I _{OZ}	I/O Tri-State Output Leakage Current	$T_A = 25^{\circ}C, \overline{OE} = 0 \text{ V}$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ

TOTAL STATIC POWER CONSUMPTION (I_{CCA} + I_{CCB})

		•	•	•	-40°C to	o +85°C			•		
					V _{CCI}	_B (V)					1
	4.	.5	3.	.3	2.	.8	1.	8	0.	.9]
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

 $NOTE: Connect ground before applying supply voltage \ V_{CCB}. This device is designed with the feature that the power-up sequence$ of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

				-40°C to +85°C									
				V _{CCB} (V)									
			4	.5	3.	.3	2	.8	1.	.8	1.	2	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t _{PHL} (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(14010-1)	A _n to B _n	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t _{PZH} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PZL} (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{PHZ} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PLZ}	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	ŌĒ to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{OSHL} ,	Output to	4.5		0.15		0.15		0.15		0.15		0.15	nS
toslh	Output Skew,	3.3		0.15		0.15		0.15		0.15		0.15	
(Note 1)	Time	2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figure 3.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

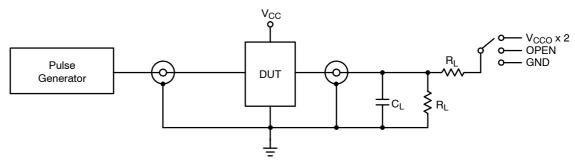


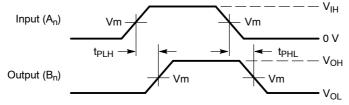
Figure 3. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

 C_L = 15 pF or equivalent (includes probe and jig capacitance)

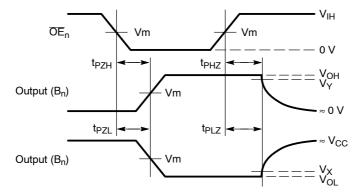
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 – Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 - Output Enable and Disable Times

 t_{R} = t_{F} = 2.0 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

			V _{CC}		
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V
V _{mA}	V _{CCA} /2				
V _{mB}	V _{CCB} /2				
V _X	V _{OL} x 0.1				
V _Y	V _{OH} x 0.9				

ORDERING INFORMATION

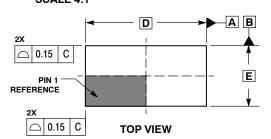
Device	Package	Shipping [†]
NLSV8T244MUTAG	UQFN20 (Pb-Free)	3000 / Tape & Reel
NLSV8T244DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLSV8T244DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



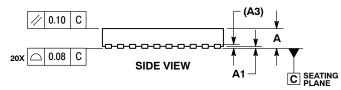
UDFN20 4x2, 0.4P CASE 517AK-01 **ISSUE O**

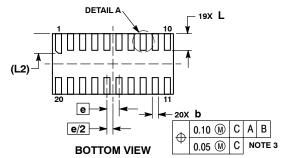
DATE 14 NOV 2006



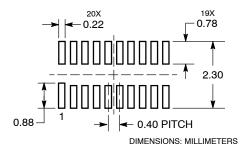


NOTE 5





MOUNTING FOOTPRINT **SOLDERMASK DEFINED**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
- MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
- 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.13	REF		
b	0.15	0.25		
D	4.00	BSC		
Е	2.00	BSC		
е	0.40	BSC		
L	0.50	0.60		
L1	0.00	0.03		
L2	0.60	0.70		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON23419D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UDFN20 4 X 2, 0.4P		PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

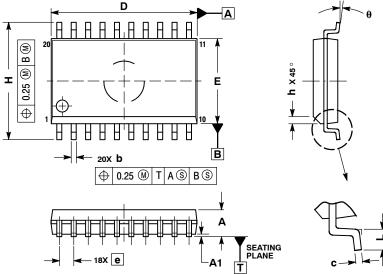




SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

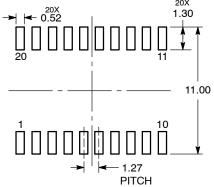
SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

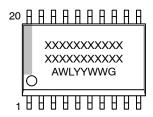
	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1

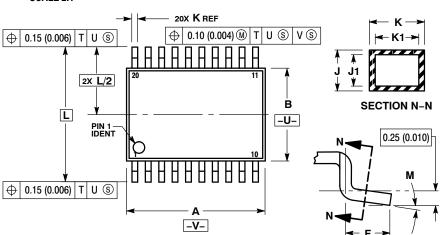
ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

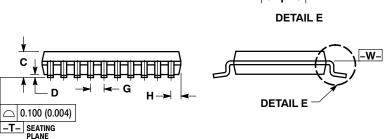
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016





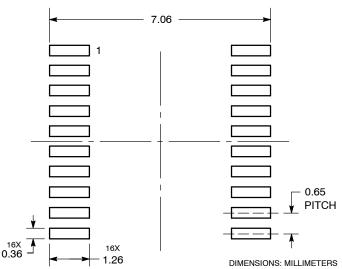
NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

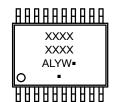
 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative